

Abstract of the Disclosure

A semiconductor lamination portion (9) including an active layer (4) is formed on a substrate (1). The semiconductor lamination portion is made of, for example, a nitride material having a cleavage plane not parallel to a cleavage plane of the substrate (1) and has a resonance cavity end faces (6) from which a laser beam is emitted. And a metal layer portion (5) is provided between the substrate and the active layer in a vicinity of the resonance cavity end faces. As a result, even if a crack is caused between the substrate and the semiconductor lamination portion, an extension of the crack stops at the metal layer portion, thereby the crack does not reach to the active layer at the resonance cavity end faces, and the cleavage plane free from any crack can be obtained at the resonance cavity end faces. Therefore, as an absorption loss at the resonance cavity end faces is reduced, the semiconductor laser which is driven with low operating current and has high reliability can be obtained.